HY860F

ABSOLUTE MAXIMUM RATINGS AT TA=25° C

PARAMETER	MAXIMUM RATING	UNIT
IR Diode continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	75	mW (No c 1)
IR Diode Peak Forward Current (Pulse Wide= 10uS, 300 pps)	1	A
Diode Power Dissipation	100	mW(No. c1)
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter- Collector Voltage	5	V
Operating Temperature Range	-55 ℃ to +100 ℃	
Storage Temperature Range	-55 ℃ to +100° C	
Lead Soldering Temperature [1.6mm(.063")From Case]	260° C for 5 seconds	

Note1. Derate Linearly 1.33mW/C from 25℃

NOTES:

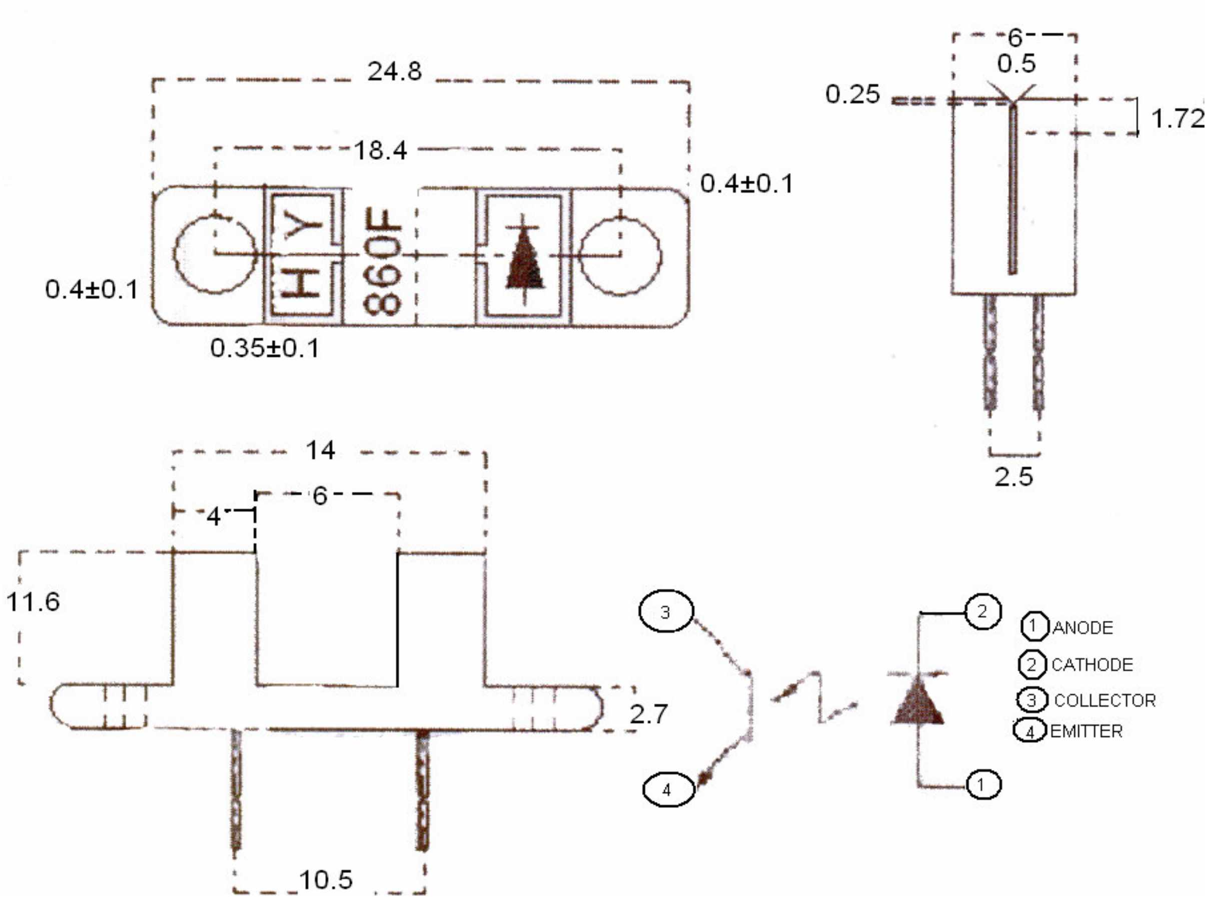
1. All dimensions are in millimeters(inches)
2. Tolerance is ±0.25mm (.010") unless otherwise noted.

FEATURES

- NON-CONTACT SWITCHING
- FOR DIRECT PC BOARD OR DUAL-IN-LINE SOCKET MOUNTING
- FAST SWITCHING SPEED

PACKAGE DIAMENSIONS

HY860F



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